

# K L Wang

## List of Publications by Year in descending order

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280  
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284  
docs citations

284  
times ranked

5428  
citing authors

#	ARTICLE	IF	CITATIONS
1	Low-power non-volatile spintronic memory: STT-RAM and beyond. Journal Physics D: Applied Physics, 2013, 46, 074003.	1.3	391
2	Ultra-low switching energy and scaling in electric-field-controlled nanoscale magnetic tunnel junctions with high resistance-area product. Applied Physics Letters, 2016, 108, .	1.5	186
3	Experimental proof-of-principle investigation of enhanced Z3DT in (001) oriented Si/Ge superlattices. Applied Physics Letters, 2000, 77, 1490-1492.	1.5	169
4	Switching current reduction using perpendicular anisotropy in CoFeB/MgO magnetic tunnel junctions. Applied Physics Letters, 2011, 98, .	1.5	169
5	High-mobility channel metal-oxide-semiconductor field-effect transistor on strained Si. Applied Physics Letters, 1993, 62, 2853-2855.	1.5	158
6	Observation of magnetic-field-induced delocalization: Transition from Anderson insulator to quantum Hall conductor. Physical Review Letters, 1993, 71, 1439-1442.	2.9	158
7	Controlled arrangement of self-organized Ge islands on patterned Si (001) substrates. Applied Physics Letters, 1999, 75, 2752-2754.	1.5	144
8	Measurements of anisotropic thermoelectric properties in superlattices. Applied Physics Letters, 2002, 81, 3588-3590.	1.5	137
9	Raman spectroscopy of electrochemically self-assembled CdS quantum dots. Applied Physics Letters, 2000, 76, 137-139.	1.5	136
10	Optical transitions in a step quantum well. Journal of Applied Physics, 1989, 65, 4377-4381.	1.1	117
11	Wet oxidation of GeSi strained layers by rapid thermal processing. Applied Physics Letters, 1990, 57, 369-371.	1.5	117
12	Simultaneous measurements of Seebeck coefficient and thermal conductivity across superlattice. Applied Physics Letters, 2002, 80, 1758-1760.	1.5	117
13	Si <sub>1-x</sub> Ge <sub>x</sub> /Si multiple quantum well infrared detector. Applied Physics Letters, 1991, 59, 2588-2590.	1.5	113
14	Changes in luminescence emission induced by proton irradiation: InGaAs/GaAs quantum wells and quantum dots. Applied Physics Letters, 2000, 76, 2074-2076.	1.5	106
15	Low writing energy and sub nanosecond spin torque transfer switching of in-plane magnetic tunnel junction for spin torque transfer random access memory. Journal of Applied Physics, 2011, 109, .	1.1	99
16	Regimented placement of self-assembled Ge dots on selectively grown Si mesas. Applied Physics Letters, 2000, 76, 3591-3593.	1.5	97
17	In-plane lattice thermal conductivity of a quantum-dot superlattice. Journal of Applied Physics, 2000, 88, 696-699.	1.1	94
18	Intersubband absorption in boron-doped multiple Ge quantum dots. Applied Physics Letters, 1999, 74, 185-187.	1.5	93

#	ARTICLE	IF	CITATIONS
19	Microscopic structure of interfaces in Si <sub>1-x</sub> Ge <sub>x</sub> /Si heterostructures and superlattices studied by x-ray scattering and fluorescence yield. Physical Review B, 1993, 47, 16373-16381.	1.1	92
20	Rapid thermal oxidation of GeSi strained layers. Applied Physics Letters, 1990, 56, 66-68.	1.5	87
21	Intersubband optical absorption in coupled quantum wells under an applied electric field. Physical Review B, 1988, 38, 8377-8382.	1.1	86
22	Epitaxial growth of high mobility Bi <sub>2</sub> Se <sub>3</sub> thin films on CdS. Applied Physics Letters, 2011, 98, 242102.	1.5	85
23	Resonant tunneling through a Si/GeSi <sub>1-x</sub> /Si heterostructure on a GeSi buffer layer. Applied Physics Letters, 1988, 53, 204-206.	1.5	82
24	Deep subnanosecond spin torque switching in magnetic tunnel junctions with combined in-plane and perpendicular polarizers. Applied Physics Letters, 2011, 98, .	1.5	82
25	Intersubband absorption in Si <sub>1-x</sub> Ge <sub>x</sub> /Si multiple quantum wells. Applied Physics Letters, 1990, 57, 2585-2587.	1.5	79
26	Chemical Etching of Si <sub>1-x</sub> Ge <sub>x</sub> in HF:H <sub>2</sub> O:H <sub>2</sub> O <sub>2</sub> :CH <sub>3</sub> COOH. J. 1260-1266.	1.3	79
27	Giant voltage modulation of magnetic anisotropy in strained heavy metal/magnet/insulator heterostructures. Physical Review B, 2015, 92, .	1.1	79
28	Normal incidence infrared detector using p-type SiGe/Si multiple quantum wells. Applied Physics Letters, 1992, 60, 103-105.	1.5	77
29	Determination of interface and bulk trap states of IGFETs using deep level transient spectroscopy. Journal of Applied Physics, 1976, 47, 4574-4577.	1.1	75
30	Magnetically doped semiconducting topological insulators. Journal of Applied Physics, 2012, 112, .	1.1	75
31	Nanometer scale patterning of silicon (100) surfaces by an atomic force microscope operating in air. Applied Physics Letters, 1994, 64, 2133-2135.	1.5	73
32	Large Stark shifts of the local to global state intersubband transitions in step quantum wells. Applied Physics Letters, 1990, 56, 1986-1988.	1.5	70
33	Intervalence subband transition in SiGe/Si multiple quantum wells normal incident detection. Applied Physics Letters, 1992, 61, 681-683.	1.5	69
34	A surfactant-mediated relaxed Si <sub>0.5</sub> Ge <sub>0.5</sub> graded layer with a very low threading dislocation density and smooth surface. Applied Physics Letters, 1999, 75, 1586-1588.	1.5	68
35	Formalism of the Kronig-Penney model for superlattices of variable basis. Physical Review B, 1988, 38, 13307-13315.	1.1	64
36	Electron mobility enhancement from coupled wells in delta-doped GaAs. Applied Physics Letters, 1993, 62, 504-506.	1.5	64

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37	Giant negative magnetoresistance of a degenerate two-dimensional electron gas in the variable-range-hopping regime. <i>Physical Review B</i> , 1992, 46, 12830-12833.	1.1	63
38	Novel infrared band-aligned superlattice laser. <i>Applied Physics Letters</i> , 1987, 51, 1404-1406.	1.5	61
39	Interdiffusion in a symmetrically strained Ge/Si superlattice. <i>Applied Physics Letters</i> , 1989, 54, 1253-1255.	1.5	61
40	Towards Si <sub>1-x</sub> Gex quantum-well resonant-state terahertz laser. <i>Applied Physics Letters</i> , 2001, 79, 3909-3911.	1.5	60
41	Normal-incidence strained-layer superlattice Ge <sub>0.5</sub> Si <sub>0.5</sub> /Si photodiodes near 1.3 $\mu$ m. <i>Applied Physics Letters</i> , 1995, 67, 566-568.	1.5	58
42	Observation of large oscillator strengths for both $\Gamma^2$ and $\Gamma^3$ intersubband transitions of step quantum wells. <i>Applied Physics Letters</i> , 1990, 56, 1046-1048.	1.5	57
43	Wet oxidation of GeSi at 700 $^{\circ}$ C. <i>Journal of Applied Physics</i> , 1992, 71, 4015-4018.	1.1	55
44	Damage and strain in epitaxial GexSi <sub>1-x</sub> films irradiated with Si. <i>Journal of Applied Physics</i> , 1993, 74, 6039-6045.	1.1	54
45	Optical and acoustic phonon modes in self-organized Ge quantum dot superlattices. <i>Applied Physics Letters</i> , 2000, 76, 586-588.	1.5	54
46	Defect distribution near the surface of electron-irradiated silicon. <i>Applied Physics Letters</i> , 1978, 33, 547-548.	1.5	53
47	Band structure and symmetry analysis of coherently grown Si <sub>1-x</sub> Gex alloys on oriented substrates. <i>Physical Review B</i> , 1993, 47, 1936-1953.	1.1	53
48	Thermoelectric figure of merit enhancement in a quantum dot superlattice. <i>Nanotechnology</i> , 2000, 11, 327-331.	1.3	50
49	High-quality Bi <sub>2</sub> Te <sub>3</sub> thin films grown on mica substrates for potential optoelectronic applications. <i>Applied Physics Letters</i> , 2013, 103, .	1.5	50
50	Effect of resistance-area product on spin-transfer switching in MgO-based magnetic tunnel junction memory cells. <i>Applied Physics Letters</i> , 2011, 98, .	1.5	49
51	High-quality strain-relaxed SiGe alloy grown on implanted silicon-on-insulator substrate. <i>Applied Physics Letters</i> , 2000, 76, 2680-2682.	1.5	48
52	Nanoscale magnetic tunnel junction sensors with perpendicular anisotropy sensing layer. <i>Applied Physics Letters</i> , 2012, 101, 062412.	1.5	48
53	Electric-field-driven magnetization switching and nonlinear magnetoelasticity in Au/FeCo/MgO heterostructures. <i>Scientific Reports</i> , 2016, 6, 29815.	1.6	48
54	Hole intersubband absorption in $\delta$ -doped multiple Si layers. <i>Applied Physics Letters</i> , 1991, 58, 1083-1085.	1.5	47

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55	Tunnel diodes fabricated from CdSe nanocrystal monolayers. Applied Physics Letters, 1999, 74, 317-319.	1.5	46
56	Raman scattering from a self-organized Ge dot superlattice. Applied Physics Letters, 1999, 74, 1863-1865.	1.5	46
57	Interdiffusion measurements in asymmetrically strained SiGe/Si superlattices. Applied Physics Letters, 1990, 56, 2628-2630.	1.5	45
58	Detection of magnetic resonance on photoluminescence from a Si/Si <sub>1-x</sub> Ge <sub>x</sub> strained-layer superlattice. Physical Review Letters, 1990, 65, 1247-1250.	2.9	44
59	Normal incidence infrared detector using intervalence subband transitions in Si <sub>1-x</sub> Ge <sub>x</sub> /Si quantum wells. Applied Physics Letters, 1992, 61, 2434-2436.	1.5	44
60	High-quality strain-relaxed SiGe films grown with low temperature Si buffer. Journal of Applied Physics, 2001, 89, 8279-8283.	1.1	43
61	Cross-plane thermal conductivity of self-assembled Ge quantum dot superlattices. Physical Review B, 2003, 67, .	1.1	43
62	Growth and characterization of molecular beam epitaxial GaAs layers on porous silicon. Applied Physics Letters, 1987, 51, 814-816.	1.5	42
63	Temperature effect on the formation of uniform self-assembled Ge dots. Applied Physics Letters, 2003, 83, 2847-2849.	1.5	41
64	Electric field control and effect of Pd capping on magnetocrystalline anisotropy in FePd thin films: A first-principles study. Physical Review B, 2014, 89, .	1.1	41
65	Boron surface segregation in silicon molecular beam epitaxy. Applied Physics Letters, 1988, 53, 48-50.	1.5	40
66	SiGe band engineering for MOS, CMOS and quantum effect devices. Journal of Materials Science: Materials in Electronics, 1995, 6, 311-324.	1.1	40
67	Compliant effect of low-temperature Si buffer for SiGe growth. Applied Physics Letters, 2001, 78, 454-456.	1.5	40
68	Dependence of tunneling current on structural variations of superlattice devices. Applied Physics Letters, 1985, 46, 167-168.	1.5	39
69	Interband resonant tunneling in InAs/AlSb/GaSb symmetric polytype structures. Physical Review B, 1992, 46, 16012-16017.	1.1	39
70	Intersubband transitions in p-type $\delta$ -doped SiGe/Si quantum well. Physical Review B, 1993, 47, 15638-15647.	1.1	39
71	High-quality Ge films on Si substrates using Sb surfactant-mediated graded SiGe buffers. Applied Physics Letters, 2001, 79, 3431-3433.	1.5	39
72	Optical phonons in self-assembled Ge quantum dot superlattices: Strain relaxation effects. Journal of Applied Physics, 2002, 92, 6804-6808.	1.1	39

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73	Enhancement of microwave emission in magnetic tunnel junction oscillators through in-plane field orientation. Applied Physics Letters, 2011, 99, .	1.5	39
74	Γ <sup>+</sup> and X <sup>+</sup> state influences on resonant tunneling current in single- and double- barrier GaAs/AlAs structures. Applied Physics Letters, 1989, 54, 1341-1343.	1.5	37
75	Intersubband absorption in Sb <sup>+</sup> -doped Si/Si <sup>1-x</sup> Gex quantum well structures grown on Si (110). Applied Physics Letters, 1992, 60, 2264-2266.	1.5	37
76	Nanometer-structure writing on Si(100) surfaces using a non-contact-mode atomic force microscope. Applied Physics Letters, 1994, 65, 1415-1417.	1.5	37
77	SiGe quantum dots prepared on an ordered mesoporous silica coated Si substrate. Applied Physics Letters, 1997, 71, 2448-2450.	1.5	36
78	Transport study of a single bismuth nanowire fabricated by the silver and silicon nanowire shadow masks. Applied Physics Letters, 2006, 89, 141503.	1.5	36
79	Uniformity and crystalline quality of CoSi <sub>2</sub> /Si heterostructures grown by molecular beam epitaxy and reactive deposition epitaxy. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1985, 3, 596.	1.6	35
80	Observation of large Stark shift in GexSi <sup>1-x</sup> /Si multiple quantum wells. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1990, 8, 217.	1.6	35
81	Effect of channel doping on the low-frequency noise in GaN/AlGaN heterostructure field-effect transistors. Applied Physics Letters, 1999, 75, 2064-2066.	1.5	35
82	A novel technique for studying electric field effect of carrier emission from a deep level center. Applied Physics Letters, 1983, 42, 838-840.	1.5	34
83	Hole transport through minibands of a symmetrically strained GexSi <sup>1-x</sup> /Si superlattice. Applied Physics Letters, 1989, 54, 1564-1566.	1.5	34
84	Nanocrystalline Ge in SiO <sub>2</sub> by annealing of GexSi <sup>1-x</sup> O <sub>2</sub> in hydrogen. Applied Physics Letters, 1993, 62, 3321-3323.	1.5	34
85	Defect spatial distributions in annealed ion-implanted silicon measured by a transient capacitance technique. Applied Physics Letters, 1976, 29, 700-702.	1.5	33
86	Investigation of flicker noise and deep-levels in GaN/AlGaN transistors. Journal of Electronic Materials, 2000, 29, 297-301.	1.0	33
87	The effect of phosphorus ion implantation on molybdenum/silicon contacts. Journal of Applied Physics, 1981, 52, 4027-4032.	1.1	32
88	Observation of inter-sub-level transitions in modulation-doped Ge quantum dots. Applied Physics Letters, 1999, 75, 1745-1747.	1.5	32
89	Effective compliant substrate for low-dislocation relaxed SiGe growth. Applied Physics Letters, 2001, 78, 1219-1221.	1.5	32
90	Photoluminescence of hydrogenated Si <sub>m</sub> Ge <sub>n</sub> superlattices. Applied Physics Letters, 1991, 59, 1705-1707.	1.5	31

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91	Field-Free Switching of Perpendicular Magnetization through Voltage-Gated Spin-Orbit Torque. , 2019, , .		30
92	A transient optical reflectivity study of laser annealing of ion-implanted silicon: Thresholds and kinetics. Applied Physics Letters, 1979, 34, 363-365.	1.5	29
93	An investigation on surface conditions for Si molecular beam epitaxial (MBE) growth. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1985, 3, 1035-1039.	0.9	29
94	Molecular beam epitaxial growth of CoSi <sub>2</sub> on porous Si. Applied Physics Letters, 1987, 51, 1809-1811.	1.5	29
95	Selective Etching of SiGe on SiGe/Si Heterostructures. Journal of the Electrochemical Society, 1991, 138, 202-204.	1.3	29
96	Demonstration of Si homojunction far-infrared detectors. Applied Physics Letters, 1998, 72, 2307-2309.	1.5	29
97	One-dimensional transport in quantum well wire-high electron mobility transistor. Applied Physics Letters, 1986, 49, 1738-1740.	1.5	28
98	Growth and study of self-organized Ge quantum wires on Si(111) substrates. Applied Physics Letters, 1999, 74, 2471-2473.	1.5	28
99	NONVOLATILE SPINTRONICS: PERSPECTIVES ON INSTANT-ON NONVOLATILE NANOELECTRONIC SYSTEMS. Spin, 2012, 02, 1250009.	0.6	28
100	Reduction of switching current density in perpendicular magnetic tunnel junctions by tuning the anisotropy of the CoFeB free layer. Journal of Applied Physics, 2012, 111, 07C907.	1.1	28
101	Strain relief of metastable GeSi layers on Si(100). Journal of Applied Physics, 1994, 75, 4475-4481.	1.1	27
102	Spin-wave utilization in a quantum computer. Physical Review A, 2001, 64, .	1.0	27
103	Nanostructure and temperature-dependent photoluminescence of Er-doped Y <sub>2</sub> O <sub>3</sub> thin films for micro-optoelectronic integrated circuits. Journal of Applied Physics, 2006, 100, 073512.	1.1	27
104	Two dimensional crystal tunneling devices for THz operation. Applied Physics Letters, 2012, 101, .	1.5	27
105	Electric-field-induced thermally assisted switching of monodomain magnetic bits. Journal of Applied Physics, 2013, 113, .	1.1	27
106	Boron oxide interaction with silicon in silicon molecular beam epitaxy. Applied Physics Letters, 1986, 49, 847-849.	1.5	26
107	Growth and characterization of Ge/Si strained-layer superlattices. Applied Physics Letters, 1988, 53, 1835-1837.	1.5	26
108	100-nm-wide silicon-insulator structures by Si molecular beam epitaxy growth on porous silicon. Applied Physics Letters, 1986, 48, 1793-1795.	1.5	25

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109	Photoluminescence and optically detected magnetic resonance of Si/Si <sup>1-x</sup> Gex strained-layer superlattices grown by molecular-beam epitaxy. Physical Review B, 1993, 47, 1305-1315.	1.1	25
110	Primary defects in low-fluence ion-implanted silicon. Applied Physics Letters, 1980, 36, 48-50.	1.5	24
111	Intersubband infrared absorption in GexSi <sup>1-x</sup> /Si superlattice by photocurrent measurement. Applied Physics Letters, 1990, 56, 1342-1344.	1.5	24
112	Infrared multispectral detection using Si/SixGe <sup>1-x</sup> quantum well infrared photodetectors. Applied Physics Letters, 2001, 78, 495-497.	1.5	24
113	Studies of molecular-beam epitaxy growth of GaAs on porous Si substrates. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1988, 6, 696.	1.6	23
114	Optical properties of Y2O3 thin films doped with spatially controlled Er <sup>3+</sup> by atomic layer deposition. Journal of Applied Physics, 2007, 101, .	1.1	23
115	Frequency and power limit of quantum well oscillators. Applied Physics Letters, 1986, 48, 1003-1005.	1.5	22
116	Interface properties of thin oxides grown on strained GexSi <sup>1-x</sup> layer. Journal of Applied Physics, 1994, 76, 982-986.	1.1	21
117	Modification of the three-phonon Umklapp process in a quantum wire. Applied Physics Letters, 2001, 79, 851-853.	1.5	21
118	Perpendicular magnetic tunnel junction with W seed and capping layers. Journal of Applied Physics, 2017, 121, .	1.1	21
119	Induced interface interactions in Ti/Si systems by ion implantation. Journal of Vacuum Science and Technology, 1979, 16, 130-133.	1.9	20
120	Defects in Q-switched laser annealed silicon. Journal of Applied Physics, 1983, 54, 3839-3848.	1.1	20
121	New silicon-on-insulator technology using a two-step oxidation technique. Applied Physics Letters, 1986, 49, 1104-1106.	1.5	20
122	Si/GexSi <sup>1-x</sup> /Si resonant tunneling diode doped by thermal boron source. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1989, 7, 327.	1.6	20
123	SiGe resonant tunneling hot-carrier transistor. Applied Physics Letters, 1990, 56, 1061-1063.	1.5	20
124	Study of Si/GeSi <sup>p</sup> heterostructures. Journal of Applied Physics, 1991, 69, 6674-6678.	1.1	20
125	Tunable normal incidence Ge quantum dot midinfrared detectors. Journal of Applied Physics, 2004, 96, 773-776.	1.1	20
126	Influence of substrate type and quality on carrier mobility in graphene nanoribbons. Journal of Applied Physics, 2013, 114, .	1.1	20



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127	Quantum devices using SiGe/Si heterostructures. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1991, 9, 2064.	1.6	19
128	Enhancement of Si hole mobility in coupled delta-doped wells. Applied Physics Letters, 1993, 62, 3455-3457.	1.5	19
129	In-plane magnetic field effect on switching voltage and thermal stability in electric-field-controlled perpendicular magnetic tunnel junctions. AIP Advances, 2016, 6, 075014.	0.6	19
130	X-ray studies of heat treated SiGe/Si strained-layer superlattices. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1990, 8, 254.	1.6	18
131	Instability of a $\text{Ge}_x\text{Si}_{1-x}\text{O}_2$ film on a $\text{Ge}_x\text{Si}_{1-x}$ layer. Journal of Applied Physics, 1992, 72, 4444-4446.	1.1	18
132	Growth of $\text{I}^2\text{-SiC}$ film on Si substrate by surface reaction using hydrocarbon gas and Si molecular beams in ultrahigh vacuum. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1992, 10, 930.	1.6	17
133	Strain in epitaxial $\text{CoSi}_2$ films on $\text{Si}(111)$ and inference for pseudomorphic growth. Applied Physics Letters, 1989, 55, 1874-1876.	1.5	16
134	Oscillator strength for intersubband transitions in strained n-type $\text{Si}_x\text{Ge}_{1-x}$ quantum wells. Physical Review B, 1992, 46, 7682-7690.	1.1	16
135	Luminescence of strained $\text{Si}_{1-x}\text{Ge}_x$ alloy layers grown by molecular beam epitaxy. Applied Physics Letters, 1992, 61, 2586-2588.	1.5	16
136	Boron delta-doped Si metal semiconductor field-effect transistor grown by molecular beam epitaxy. Applied Physics Letters, 1993, 63, 1363-1365.	1.5	16
137	Insight into the antiferromagnetic structure manipulated by electronic reconstruction. Physical Review B, 2016, 94, .	1.1	16
138	Analog to Stochastic Bit Stream Converter Utilizing Voltage-Assisted Spin Hall Effect. IEEE Electron Device Letters, 2017, 38, 1343-1346.	2.2	16
139	Study of $\text{CoSi}_2/\text{Si}$ strained layers grown by molecular beam epitaxy. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1987, 5, 745.	1.6	15
140	Electron intersubband absorption in $\text{Ge}/\text{Si}_{1-x}\text{Ge}_x$ quantum well structures grown on Si (001) substrate. Applied Physics Letters, 1994, 64, 1256-1258.	1.5	15
141	Interfacial roughness scaling and strain in lattice mismatched $\text{Si}_{0.4}\text{Ge}_{0.6}$ thin films on Si. Applied Physics Letters, 1995, 67, 629-631.	1.5	15
142	Far-infrared free-hole absorption in epitaxial silicon films for homojunction detectors. Applied Physics Letters, 1997, 71, 515-517.	1.5	15
143	Temperature-dependent morphology of three-dimensional InAs islands grown on silicon. Applied Physics Letters, 1999, 75, 1273-1275.	1.5	15
144	A Spintronic Voltage-Controlled Stochastic Oscillator for Event-Driven Random Sampling. IEEE Electron Device Letters, 2017, 38, 281-284.	2.2	15

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145	Interband optical transitions in GaAs-Ga <sub>1-x</sub> Al <sub>x</sub> As superlattices in an applied electric field. Physical Review B, 1987, 35, 653-659.	1.1	14
146	Formation of nanometer-scale InAs islands on silicon. Journal of Electronic Materials, 1999, 28, 432-436.	1.0	14
147	Defect formation chemistry of EL2 center at E <sub>c</sub> + 0.83 eV in ion-implanted gallium arsenide. Journal of Applied Physics, 1982, 53, 8653-8662.	1.1	13
148	Free-electron density and transit time in a finite superlattice. Journal of Applied Physics, 1986, 59, 2968-2970.	1.1	13
149	Observation of a large capacitive current in a double barrier resonant tunneling diode at resonance. Applied Physics Letters, 1994, 64, 2276-2278.	1.5	13
150	Prospects for High Thermoelectric Figures of Merit in 2D Systems. Materials Research Society Symposia Proceedings, 1997, 478, 55.	0.1	13
151	Response to "Comment on "Raman scattering from a self-organized Ge dot superlattice" [Appl. Phys. Lett. 75, 3572 (1999)]. Applied Physics Letters, 1999, 75, 3574-3575.	1.5	13
152	Deep level defect study of molecular beam epitaxially grown silicon films. Applied Physics Letters, 1986, 48, 287-289.	1.5	12
153	Studies of interdiffusion in Ge/Si strained layer superlattices. Journal of Electronic Materials, 1990, 19, 125-129.	1.0	12
154	Dependence of damage and strain on the temperature of Si irradiation in epitaxial Ge <sub>0.10</sub> Si <sub>0.90</sub> films on Si(100). Journal of Applied Physics, 1995, 77, 2329-2338.	1.1	12
155	Sb surfactant-mediated SiGe graded layers for Ge photodiodes integrated on Si. Journal of Applied Physics, 2006, 99, 024504.	1.1	12
156	Tunable Magnetoelastic Effects in Voltage-Controlled Exchange-Coupled Composite Multiferroic Microstructures. ACS Applied Materials & Interfaces, 2020, 12, 6752-6760.	4.0	12
157	Detection sensitivity and spatial resolution of reverse-bias pulsed deep-level transient spectroscopy for studying electric field-enhanced carrier emission. Journal of Applied Physics, 1985, 57, 1016-1021.	1.1	11
158	The study of relaxation in asymmetrically strained Si <sub>1-x</sub> Ge <sub>x</sub> Si superlattices. Journal of Electronic Materials, 1991, 20, 389-394.	1.0	11
159	Temperature dependences of the E <sub>0</sub> transitions in bulk Ge and a Ge-rich (Si) <sub>m</sub> /(Ge) <sub>n</sub> superlattice. Physical Review B, 1992, 45, 1712-1718.	1.1	11
160	Characterization of Si <sub>x</sub> Ge <sub>1-x</sub> /Si heterostructures for device applications using spectroscopic ellipsometry. Journal of Applied Physics, 1993, 74, 586-595.	1.1	11
161	Boron delta doping in Si and SiGe and its application toward field-effect transistor devices. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1994, 12, 1203.	1.6	11
162	Damage and strain in pseudomorphic vs relaxed Ge <sub>x</sub> Si <sub>1-x</sub> layers on Si(100) generated by Si ion irradiation. Journal of Electronic Materials, 1994, 23, 369-373.	1.0	11

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163	Fabrication of nanometer size photoresist wire patterns with a silver nanocrystal shadowmask. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1999, 17, 1425-1427.	0.9	11
164	Interface modification of refractory metal-silicon structures by ion implantation. Journal of Vacuum Science and Technology, 1979, 16, 1909-1912.	1.9	10
165	Relationships of electrical properties and melting threshold in laser-annealed ion-implanted silicon. Applied Physics Letters, 1979, 35, 263-265.	1.5	10
166	A system for measuring deep-level spatial concentration distributions. Journal of Applied Physics, 1982, 53, 449-453.	1.1	10
167	Intersubband Auger recombination in a superlattice. Physical Review B, 1988, 37, 1328-1333.	1.1	10
168	Electronic transitions in a Si-Ge strained monolayer superlattice measured by photoreflectance. Applied Physics Letters, 1990, 56, 1498-1500.	1.5	10
169	Strain transfer between thin films on buried oxide and its application in heteroepitaxial crystal growth. Philosophical Magazine Letters, 1995, 72, 231-237.	0.5	10
170	Correlation between barrier height and band offsets in metal/Si <sub>1-x</sub> Ge <sub>x</sub> /Si heterostructures. Applied Physics Letters, 1998, 73, 3920-3922.	1.5	10
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